

**Silicon Super Fast  
Recovery Diode**

$V_{RRM} = 50\text{ V} - 600\text{ V}$

$I_F = 200\text{ A}$

**Features**

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

Twin Tower Package


**Maximum ratings, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

Parameter	Symbol	Conditions	MUR20040CT (R)	MUR20060CT (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		400	600	V
RMS reverse voltage	$V_{RMS}$		280	420	V
DC blocking voltage	$V_{DC}$		400	600	V
Continuous forward current	$I_F$	$T_C \leq 140\text{ }^\circ\text{C}$	200	200	A
Surge non-repetitive forward current, Half Sine Wave	$I_{FSM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	400	400	A
Operating temperature	$T_J$		-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	$^\circ\text{C}$

**Electrical characteristics, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	MUR20040CT (R)	MUR20060CT (R)	Unit
Diode forward voltage	$V_F$	$I_F = 50\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	1.3	1.7	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_J = 25\text{ }^\circ\text{C}$	25	25	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	1	1	mA
<b>Recovery Time</b>					
Maximum reverse recovery time	$T_{RR}$	$I_F = 0.5\text{ A}$ , $I_{RM} = 1.0\text{ A}$ , $I_{RRM} = 0.25\text{ A}$	90	110	nS

